NSN 5961-01-169-6518

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-169-6518 **Inclosure Material:** Plastic **Overall Length:** 0.886 inches **Overall Height:** 0.190 inches **Overall Width:** 0.420 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-220 **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 repetitive peak off-state voltage and 100.0 repetitive peak reverse voltage and 200.0 nonrepetitive peak off-state voltage **Current Rating Per Characteristic:** 8.00 amperes forward current, total rms nanoamperes **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0